

10/511541

DTG4 Rec'd PCT/PTO 18 OCT 2004

XA-10191
PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

KOSHIMIZU, Makoto et al.

Intl. Appln. No.: PCT/JP02/03764

Intl. Filing Date: 16 April 2002

For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

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INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Attn: Mail Stop PCT, DO/EO/US

Sir:

Pursuant to 37 C.F.R. § 1.56, and without any assertion as to materiality or prior art effect, the documents listed on the attached Form PTO-1449 are hereby cited.

Documents AI-AL on the attached List were cited in the International Search Report (copy attached). The Office should have received copies of the primary citations from the PCT International Authority. So copies are not being submitted herewith in order to avoid duplication. If the Office did not receive the copies from the PCT International Authority, the Examiner is requested to telephone the undersigned so that copies may be provided.


Documents AH and AT (copies herewith) are cited in the specification, on pages 2-3, and their relevance is indicated therein.

Respectfully submitted,

MWS:sjk

Miles & Stockbridge P.C.
1751 Pinnacle Drive,
Suite 500
McLean, Virginia 22102-3833
(703) 903-9000

October 18, 2004

By: 
Mitchell W. Shapiro
Reg. No. 31,568

FORM PTO-1449				Atty. Docket No. XA-10191		Appln. No. 10/511541	
<u>LIST OF DOCUMENTS CITED BY APPLICANT</u>							
				Applicant KOSHIMIZU, Makoto et al.			
				Filing Date Herewith		Group Art Unit	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
FOREIGN PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
	AH	2705344	10/09/97	Japan			Abstract
	AI	10-092833	04/10/98	Japan			
	AJ	63-052412	03/05/88	Japan			
	AK	06-151387	05/31/94	Japan			
	AL	11-176807	07/02/99	Japan			
	AM						
	AN						
	AO						
	AP						
	AQ						
	AR						
	AS						
OTHER (including author, title, date, pertinent pages, etc.)							
	AT	F. Sato et al., "A super self-aligned selectively grown SiGe base (SSSB) bipolar transistor fabricated by cold-wall UHV/CVD technology", IEEE Trans. ED, Vol. 41, Issue 8, August 1994, pp. 1373-1378. (Abstract Only)					
Examiner				Date Considered			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							